

# **Single 2-Input AND Gate**

## NLV74VHC1G08, NLV74VHC1GT08

The NLV74VHC1G08 / NLV74VHC1GT08 is a single 2 input AND gate in tiny footprint packages. The NLV74VHC1G08 has CMOS-level input thresholds while the NLV74VHC1GT08 has TTL-level input thresholds.

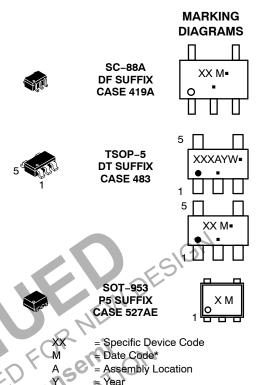
The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when  $V_{CC} = 0 \ V$  and when the output voltage exceeds  $V_{CC}.$  These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

## **Features**

- Designed for 2.0 V to 5.5 V V<sub>CC</sub> Operation
- 3.5 ns t<sub>PD</sub> at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I<sub>OFF</sub> Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A, TSOP-5 and SOT-953 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Figure 1. Logic Symbol



(Note: Microdot may be in either location)

Work Week

= Pb-Free Package

\*Date Code orientation and/or position may vary depending upon manufacturing location.

## **ORDERING INFORMATION**

See detailed ordering, marking and shipping information on page 7 of this data sheet.

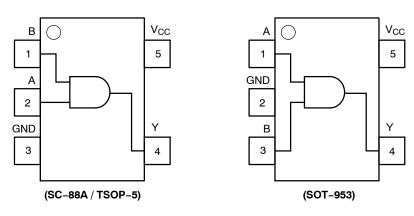


Figure 2. Pinout (Top View)

## **PIN ASSIGNMENT**

(SC-88A / TSOP-5)

Pin	Function
1	В
2	Α
3	GND
4	Y
5	V <sub>CC</sub>

## PIN ASSIGNMENT (SOT-953)

				,	
Pin	Function		Pin	Function	Input
1	В		1	Α	A
2	A		2	GND	L
3	GND		3	В	LIE
4	Y		4	Y	P.H
5	V <sub>CC</sub>		5	V <sub>CC</sub>	HU, V
THIS	DEVICE PI	N	OF RECONTAINESENTAIN	Vcc MNENDED ACTORIN	FORMAL

## **FUNCTION TABLE**

Inp	out	Output
Α	B	Y
L	17	L
FIE	Н	L
Н	L	L
Н	Ŧ	Н

## **MAXIMUM RATINGS**

Symbol	CI	naracteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	1Gxx and MC74VHC1GT08P5T5G-L22088	-0.5 to V <sub>CC</sub> + 0.5	V
		1GTxx Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> + 0.5 -0.5 to +7.0 -0.5 to +7.0	
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-20	mA
lok	DC Output Diode Current (NLV)	1Gxx and MC74VHC1GT08P5T5G-L22088 V <sub>OUT</sub> > V <sub>CC</sub> , V <sub>OUT</sub> < GND	±20	mA
		1GTxx V <sub>OUT</sub> < GND	-20	
lout	DC Output Source/Sink Current		±25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC Supply Current per Supply Pir	±50	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Ca	se for 10 secs	260	°C
T <sub>J</sub>	Junction Temperature Under Bias		+150	°C
θJA	Thermal Resistance (Note 2)	SC-88A TSOP-5 SOT-953	377 320 254	°C/W
P <sub>D</sub>	Power Dissipation in Still Air	SC-88A TSOP-5 SOT-953	332 390 491	mW
MSL	Moisture Sensitivity	I I I I I I I I I I I I I I I I I I I	Level 1	-
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V <sub>ESD</sub>	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I <sub>Latchup</sub>	Latchup Performance (Note 4)	RANIFO	± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality Stresses exceeding those listed in the Maximum Hatings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.

2. Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.

3. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

4. Tested to EIA/JESD78 Class II.

THIS DE

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	C	Characteristics	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage		0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	1Gxx and MC74VHC1GT08P5T5G-L22088	0	V <sub>CC</sub>	V
		1GTxx Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V <sub>CC</sub> = 0 V)	0 0 0	V <sub>CC</sub> 5.5 5.5	
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 3.0 V to 3.6 V V <sub>CC</sub> = 4.5 V to 5.5 V	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (NLV74VHC1G08)

		Test	V <sub>CC</sub>	1	T <sub>A</sub> = 25°	С	-40°C ≤ 7	Γ <sub>A</sub> ≤ 85°C	-55°C ≤ T	∖ ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
$V_{IH}$	High-Level Input		2.0	1.5	_	-	1.5		1.5	-	٧
	Voltage		3.0	2.1	-	-	2.1	N	2.1	_	
			4.5	3.15	-	1	3.15	R- :	3.15	-	
			5.5	3.85	1		3.85	-cill	3.85	-	
$V_{IL}$	Low-Level Input Voltage		2.0	<b>\-</b>	-	0.5	<b>-</b>	0.5	_	0.5	٧
	voltage		3.0	1		0.9	12	0.9	-	0.9	
			4.5	1	14/1	1.35		1.35	-	1.35	
			5.5		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	1.65	121	1.65	-	1.65	
V <sub>OH</sub>	High-Level Output Voltage	$\begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -50  \mu\text{A} \\ I_{OH} = -50  \mu\text{A} \\ I_{OH} = -50  \mu\text{A} \\ I_{OH} = -4  m\text{A} \\ I_{OH} = -8  m\text{A} \end{array}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5	FOF - -	1.9 2.9 4.4 2.48 3.80	- - - -	1.9 2.9 4.4 2.34 3.66	- - - -	V
V <sub>OL</sub>	Low-Level Output Voltage	$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 50  \mu\text{A} \\ I_{OL} &= 50  \mu\text{A} \\ I_{OL} &= 50  \mu\text{A} \\ I_{OL} &= 4  m\text{A} \\ I_{OL} &= 8  m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.1 0.44 0.44	- - - -	0.1 0.1 0.1 0.52 0.52	V
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	2.0 to 5.5	_	_	±0.1	-	±1.0	-	±1.0	μА
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V	0.0	-	_	1.0	-	10	-	10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	-	-	1.0	-	20	-	40	μΑ

## DC ELECTRICAL CHARACTERISTICS (NLV74VHC1GT08)

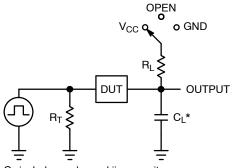
		Test	V <sub>CC</sub>	1	T <sub>A</sub> = 25°	С	-40°C ≤ 1	Γ <sub>A</sub> ≤ 85°C	-55°C ≤ T	A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input		2.0	1.0	-	-	1.0	-	1.0	-	V
	Voltage		3.0	1.4	-	-	1.4	-	1.4	-	
			4.5	2.0	-	-	2.0	-	2.0	-	
			5.5	2.0	-	-	2.0	-	2.0	-	
V <sub>IL</sub>	Low-Level Input		2.0	-	_	0.28	-	0.28	_	0.28	V
	Voltage		3.0	-	-	0.45	-	0.45	-	0.45	
			4.5	-	-	0.8	-	0.8	-	0.8	
			5.5	-	-	0.8	-	0.8	-	0.8	
V <sub>OH</sub>	High-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -50  \mu\text{A} \\ &I_{OH} = -50  \mu\text{A} \\ &I_{OH} = -50  \mu\text{A} \\ &I_{OH} = -4  m\text{A} \\ &I_{OH} = -8  m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	1.9 2.9 4.4 2.58 3.94	2.0 3.0 4.5 –		1.9 2.9 4.4 2.48 3.80	1	1.9 2.9 4.4 2.34 3.66	GN	V
V <sub>OL</sub>	Low-Level Output Voltage	$\begin{array}{c} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 50  \mu\text{A} \\ I_{OL} = 50  \mu\text{A} \\ I_{OL} = 50  \mu\text{A} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA} \end{array}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 -	0.1 0.1 0.1 0.36 0.36	-	0.1 0.1 0.1 0.44 0.44	NOE:	0.1 0.1 0.1 0.52 0.52	V
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	2.0 to 5.5	-		±0.1	FC	±1.0	MO	±1.0	μΑ
l <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0	-	-	1.0	0	10	_	10	μΑ
	Power Off Leakage Current (MC74VHC1GT08P 5T5G-L22088 Only)	V <sub>IN</sub> = 5.5 V	0			1.0	INFO	10	-	10	
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5	M	15	1.0	-	20	-	40	μΑ
I <sub>CCT</sub>	Increase in Quiescent Supply Current per Input Pin	One Input: V <sub>IN</sub> = 3.4 V; Other Input at V <sub>CC</sub> or GND	5.5	RT	14.	1.35	-	1.5	-	1.65	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS

<b>~</b>	Hi	1		$T_A = 25^{\circ}C$ $-40^{\circ}C \leq T$		T <sub>A</sub> ≤ 85°C	-55°C ≤ T	A ≤ 125°C			
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay,	C <sub>L</sub> = 15 pF	3.0 to 3.6	-	4.1	8.8	-	10.5	-	12.5	ns
t <sub>PHL</sub>	A to Y (Figures 3 and 4)	C <sub>L</sub> = 50 pF		-	5.9	12.3	-	14.0	_	16.5	1
		C <sub>L</sub> = 15 pF	4.5 to 5.5	-	3.5	5.9	-	7.0	-	9.0	
		C <sub>L</sub> = 50 pF		-	4.2	7.9	-	9.0	_	11.0	1
C <sub>IN</sub>	Input Capacitance			-	4.0	10	-	10	-	10	pF
C <sub>OUT</sub>	Output Capacitance	Output in High Impedance State		-	6.0	-	-	-	-	-	pF
Symbol	Parameter							Typical (	@ 25°C, V <sub>C</sub>	c = 5.0 V	Unit
C <sub>PD</sub>	Power Dissipation Ca	pacitance (Not	e 5)						8.0		pF

<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.



Test	Switch Position	C <sub>L</sub> , pF	$R_L, \Omega$
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	See AC Characteristics Table	Х
t <sub>PLZ</sub> / t <sub>PZL</sub>	V <sub>CC</sub>		1 k
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND		1 k

X = Don't Care

 $C_L$  includes probe and jig capacitance  $R_T$  is  $Z_{OUT}$  of pulse generator (typically 50  $\Omega)$  f = 1 MHz

Figure 3. Test Circuit

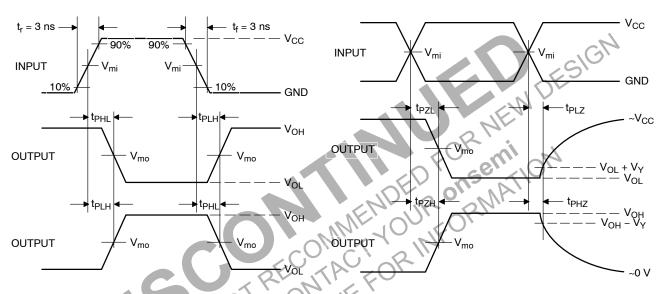


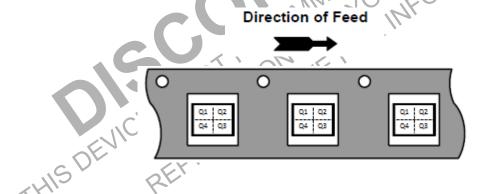
Figure 4. Switching Waveforms

	110 1 F GF	V <sub>mo</sub>	o, V	
V <sub>CC</sub> , V	V <sub>mi</sub> , v	t <sub>PLH</sub> , t <sub>PHL</sub>	$t_{PZL}$ , $t_{PLZ}$ , $t_{PZH}$ , $t_{PHZ}$	V <sub>Y</sub> , V
3.0 to 3.6	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.3
4.5 to 5.5	V <sub>CC</sub> /2	V <sub>CC</sub> /2	V <sub>CC</sub> /2	0.3

## **ORDERING INFORMATION**

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping <sup>†</sup>
MC74VHC1G08DFT1G-L22038	SC-88A	V2	Q2	3000 / Tape & Reel
MC74VHC1G08DFT2G-F22038	SC-88A	V2	Q4	3000 / Tape & Reel
NLVVHC1G08DFT1G*	SC-88A	V2	Q2	3000 / Tape & Reel
NLVVHC1G08DFT2G*	SC-88A	V2	Q4	3000 / Tape & Reel
M74VHC1GT08DFT1G-L22038	SC-88A	VT	Q2	3000 / Tape & Reel
M74VHC1GT08DFT2G-F22038	SC-88A	VT	Q4	3000 / Tape & Reel
NLVVHC1GT08DFT1G*	SC-88A	VT	Q2	3000 / Tape & Reel
NLVVHC1GT08DFT2G*	SC-88A	VT	Q4	3000 / Tape & Reel
MC74VHC1G08DTT1G	TSOP-5	V2	Q4	3000 / Tape & Reel
M74VHC1GT08DTT1G	TSOP-5	VT	Q4	3000 / Tape & Reel
NLV74VHC1G08DTT1G*	TSOP-5	V2	Q4	3000 / Tape & Reel
NLVVHC1GT08DTT1G*	TSOP-5	VT	Q4	3000 / Tape & Reel
MC74VHC1G08P5T5G-L22088	SOT-953	E	Q2	8000 / Tape & Reel
MC74VHC1GT08P5T5G-L22088	SOT-953	Р	Q2	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL





## SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

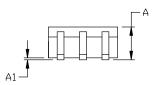
**DATE 11 APR 2023** 

### NOTES:

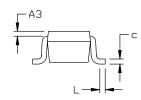
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE, NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,
  OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

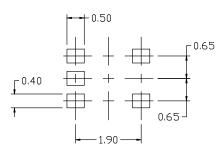
DIM	MI	LLIMETE	RS	
INITU	MIN.	N□M.	MAX.	
А	0.80	0.95	1.10	
A1			0.10	
A3		0.20 REF	•	
b	0.10	0.20	0.30	
C	0.10		0.25	
D	1.80	2.00	2,20	
Е	2.00	2.10	2.20	
E1	1.15	1.25	1.35	
е	0.65 BSC			
L	0.10	0.15	0.30	

# 5 4 E1 E1 E1 E1 E1 E1



◆ 0.2 M B M





# RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## GENERIC MARKING DIAGRAM\*



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
<ol><li>EMITTER</li></ol>
3. BASE
<ol><li>COLLECTOR</li></ol>
<ol><li>COLLECTOR</li></ol>

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1 STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4

STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

## **DOCUMENT NUMBER:**

98ASB42984B

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**DESCRIPTION:** 

5. COLLECTOR 2/BASE 1

SC-88A (SC-70-5/SOT-353)

PAGE 1 OF 1

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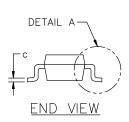


## TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483 ISSUE P**

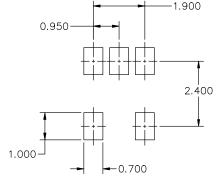
**DATE 01 APR 2024** 

## NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.



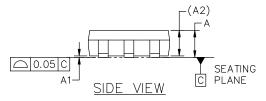
DIM	MILLIMETERS			
ININ	MIN.	NOM.	MAX.	
А	0.900	1.000	1.100	
A1	0.010	0.055	0.100	
A2	0.950 REF.			
b	0.250	0.375	0.500	
С	0.100	0.180	0.260	
D	2.850	3.000	3.150	
Е	2.500	2.750	3.000	
E1	1.350	1.500	1.650	
е	0.950 BSC			
L	0.200	0.400	0.600	
Θ	0.	5°	10°	

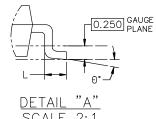


RECOMMENDED MOUNTING FOOTPRINT\*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

# NOTE 5 В Ė1 PIN 1 **IDENTIFIER** A TOP VIEW





# SCALE 2:1

## **GENERIC MARKING DIAGRAM\***





XXX = Specific Device Code

= Pb-Free Package

= Date Code

Analog Discrete/Logic

XXX = Specific Device Code

= Assembly Location = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

М

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## SOT-953 1.00x0.80x0.37, 0.35P CASE 527AE **ISSUE F**

**DATE 17 JAN 2024** 

MAX

0.40

0.20

0.17

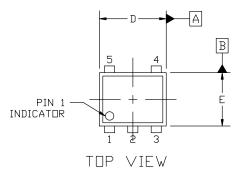
1.05

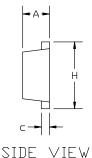
0.85

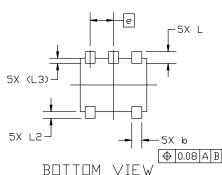
1.05

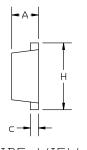
## NOTES:

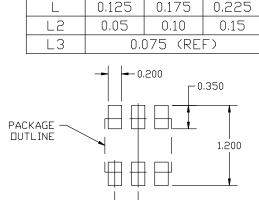
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.











MILLIMFTERS

 $N\square M$ 

0.37

0.15

0.12

1.00

0.80

0.35 BSC

1.00

MIN

0.34

0.10

0.07

0.95

0.75

0.95

DIM

Α

b

C

 $\mathbb{D}$ 

E

9 Н

## RECOMMENDED MOUNTING FOOTPRINT

0.350

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## **GENERIC MARKING DIAGRAM\***



= Specific Device Code

= Month Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-953 1.00x0.80x0.37, 0	0.35P	PAGE 1 OF 9	

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